



TO-92 Plastic-Encapsulate Transistors

STB1277 TRANSISTOR (PNP)

FEATURES

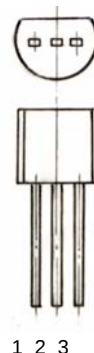
- Audio power amplifier
- High current application
- High current : $I_C = -2A$
- Complementary pair with STD1862

MAXIMUM RATINGS ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-2	A
P_C	Collector Power Dissipation	625	mW
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55-150	$^\circ C$

TO-92

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	$I_C = -100\mu A, I_E = 0$	-30			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -1mA, I_B = 0$	-30			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -1mA, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -30V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -2V, I_C = -500mA$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2A, I_B = -0.2A$			-0.8	V
Base-emitter on voltage	$V_{BE(on)}$	$V_{CE} = -2V, I_C = -500mA$			-1	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -50mA$		170		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		48		pF

CLASSIFICATION h_{FE}

Rank	O	Y
Range	100-200	160-320

Typical Characteristics

STB1277

Fig. 1 $P_C - T_a$

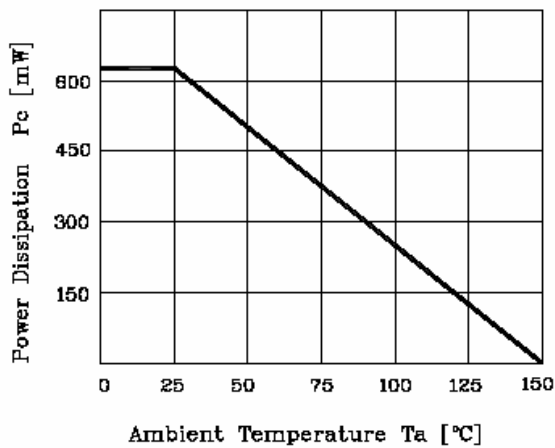


Fig. 2 $I_C - V_{BE}$

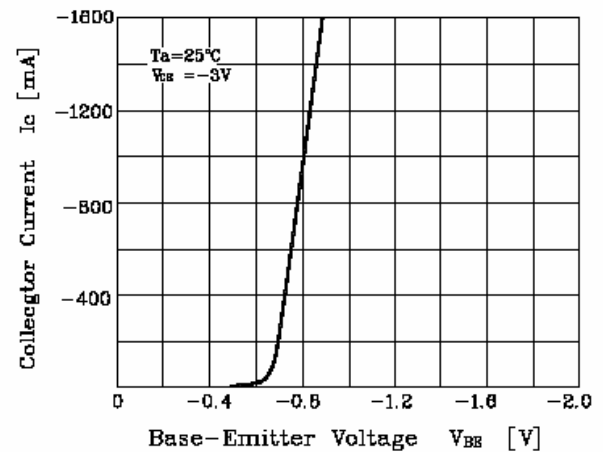


Fig. 3 $I_C - V_{CE}$

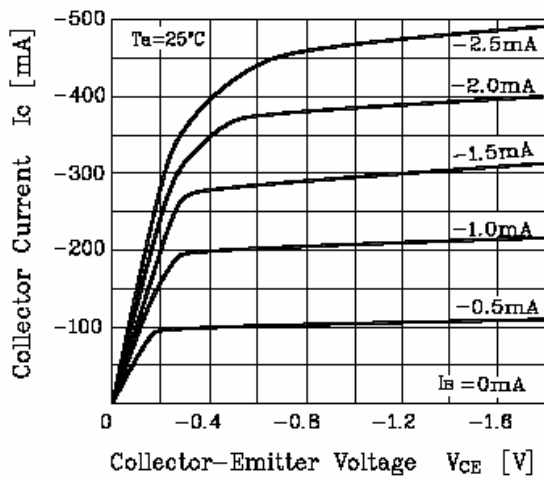


Fig. 4 $V_{CE(sat)} - I_C$

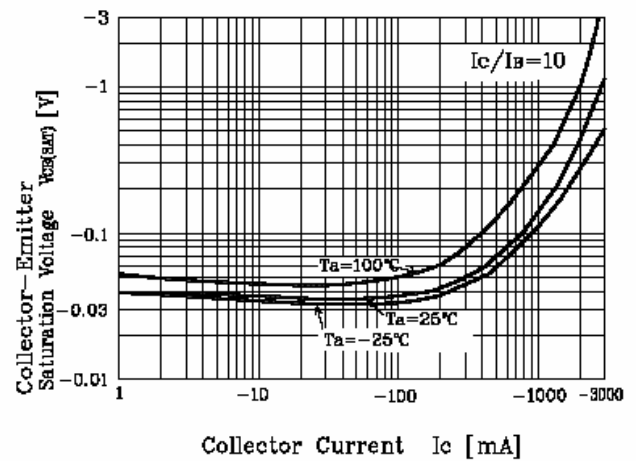


Fig. 5 $h_{FE} - I_C$

